N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	40V
I_D	340A
$R_{DS(ON)}$(at V_{GS}=10V)	1.3m
100% EAS Tested	
100% V_{DS} Tested	

General Description

Excellent package for heat dissipation
High density cell design for low $R_{DS(ON)}$
Moisture Sensitivity Level 1

R

Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D	40	-	-	V
		V_{GS}= 0V, I_D=1mA	40	-		

Typical Electrical and Thermal Characteristics Diagrams

Figure 1. Output Characteristics

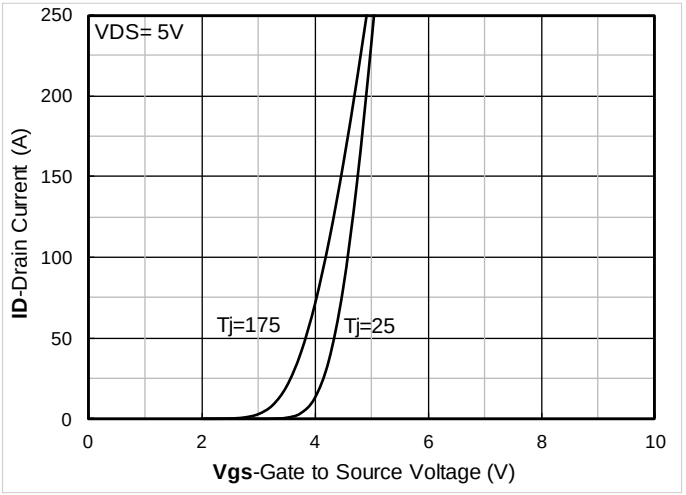


Figure 2. Transfer Characteristics

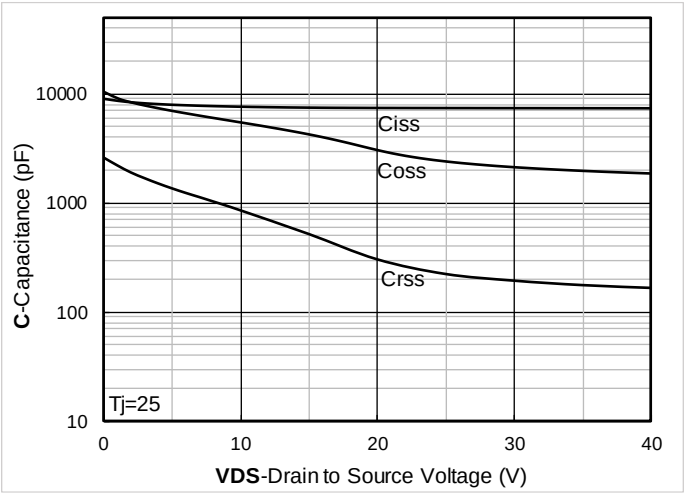


Figure 3. Capacitance Characteristics

Figure 4. Gate Charge

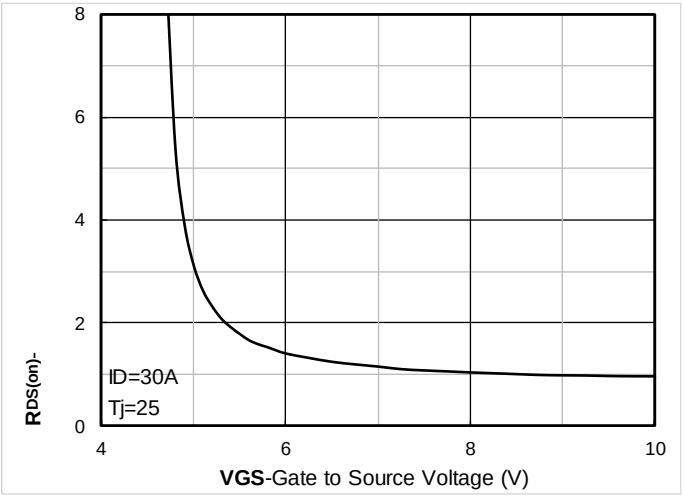


Figure 5. On-Resistance vs Gate to Source Voltage

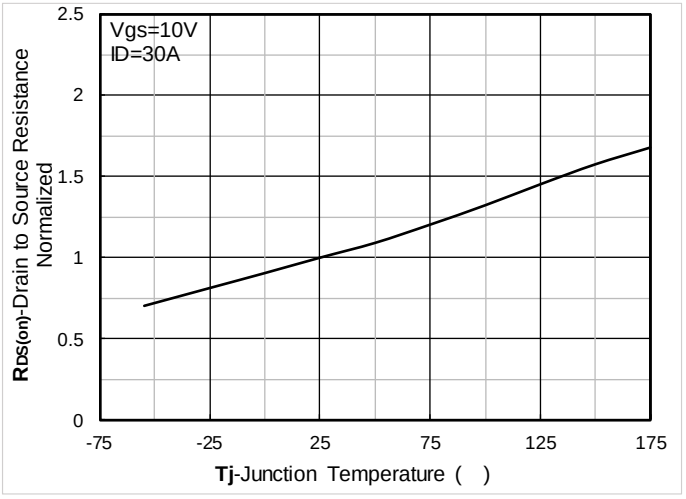
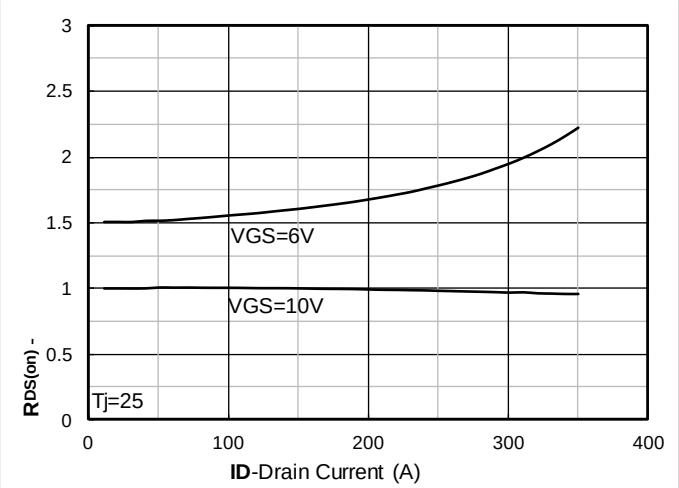


Figure 6. Normalized On-Resistance



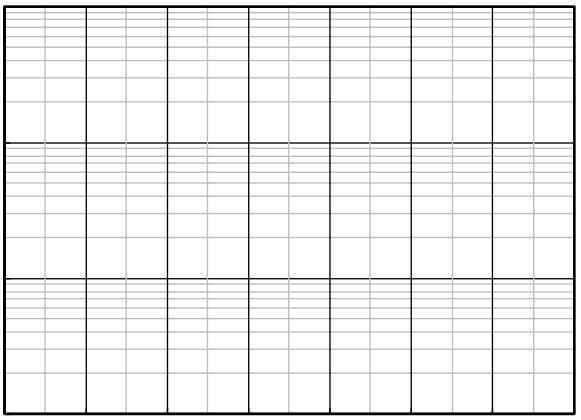


Figure 7. $R_{DS(on)}$

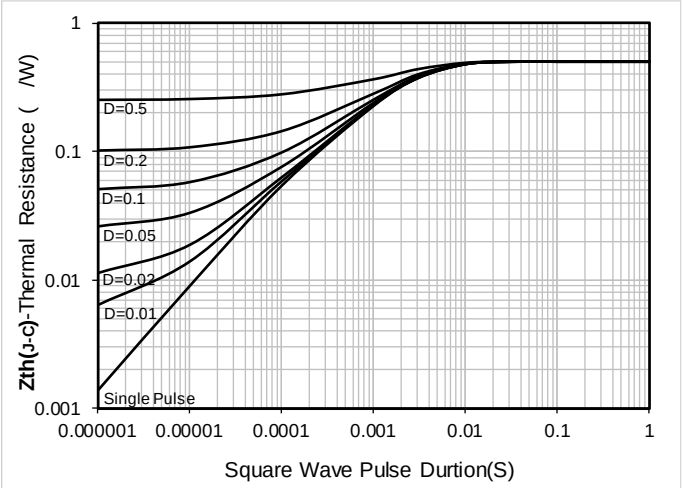


Figure 13. Maximum Transient Thermal Impedance

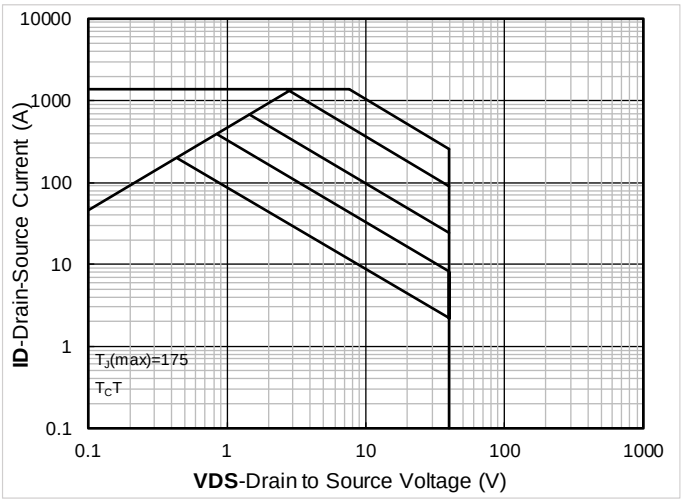


Figure 14. Safe Operation Area

Test Circuits & Waveforms

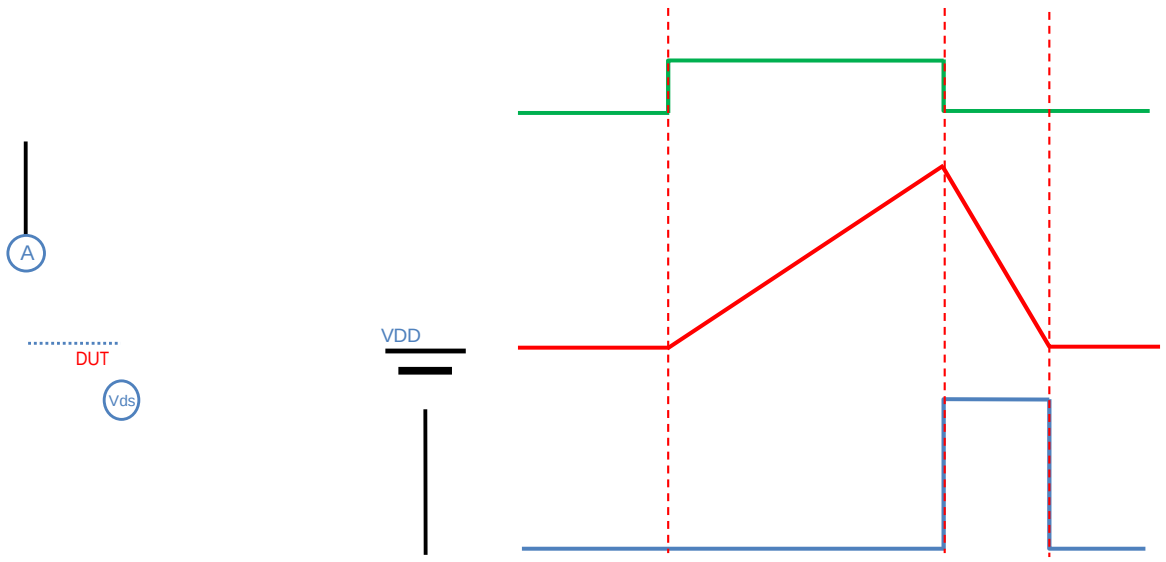


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

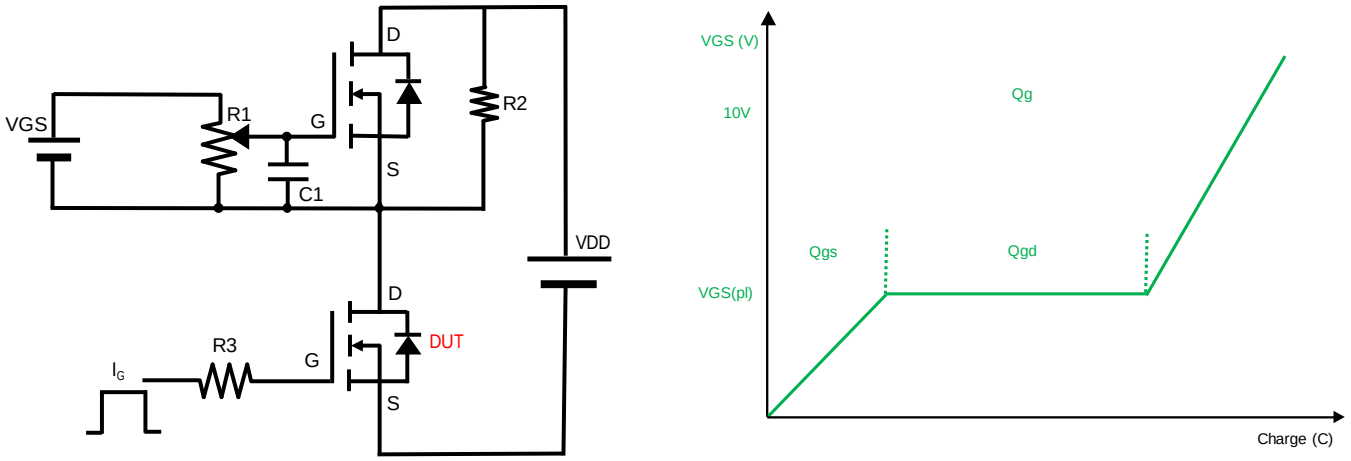


Figure B. Gate Charge Test Circuit & Waveform

TOLL Package information

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	2.2	2.3	2.4
A1	1.7	1.8	1.9
b	0.7	0.8	0.9
b1	9.7	9.8	9.9
b2	1.1	1.2	1.3
c	0.4		

Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.03mm.
3.The pad layout is for reference purposes only.

SUGGESTED SOLDER PAD LAYOUT
TOP VIEW

Disclaimer

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The product listed herein is designed to be used with automotive electronics,are not designed for use in medical, life-saving, lifesustaining,or